

TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

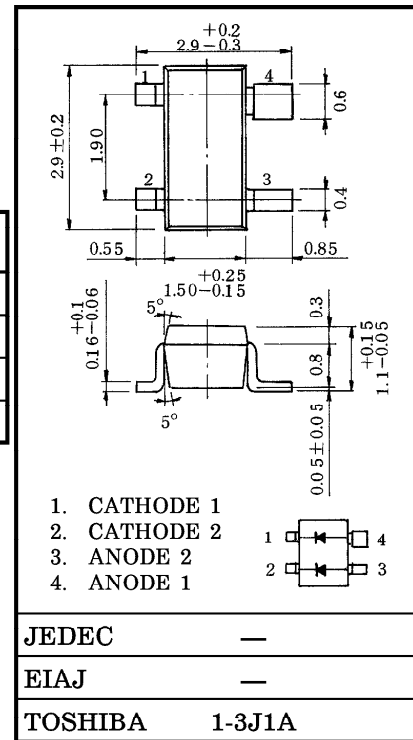
# 1SV237

VHF~UHF BAND RF ATTENUATOR APPLICATIONS.

Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$V_R$	50	V
Forward Current	$I_F$	50	mA
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_{stg}$	-55~125	°C

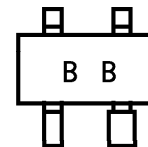


Weight : 0.013g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	$V_R$	$I_R = 10\mu A$	50	—	—	V
Reverse Current	$I_R$	$V_R = 50V$	—	—	0.1	$\mu A$
Forward Voltage	$V_F$	$I_F = 50mA$	—	0.95	—	V
Total Capacitance	$C_T$	$V_R = 50V, f = 1MHz$	—	0.25	—	pF
Series Resistance	$r_s$	$I_F = 10mA, f = 100MHz$	—	3.5	—	$\Omega$

Marking



961001EAA2

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